

英飞凌汽车级40V 175°C N沟道增强型

OptiMOS™ 6 功率晶体管

产品概述

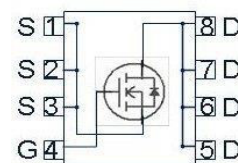
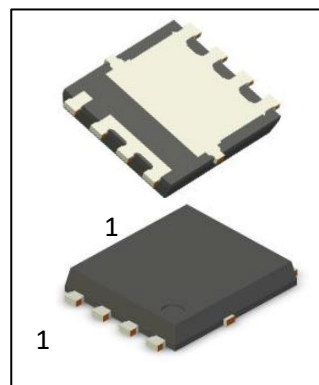
V_{DS}	40	V
$R_{DS(on),max}$	2.0	mΩ
I_D	100	A



特点

- OptiMOS™ - 用于汽车应用的功率MOSFET
- N 沟道 - 增强型 - 逻辑电平
- 通过 AEC-Q101 认证
- MSL1 回流焊峰值温度高达 260°C
- 工作温度 175°C
- 绿色产品：符合 RoHS 标准
- 100% 雪崩测试

PG-TDSON-8



Type	Package	Marking
IAUC100N04S6L020	PG-TDSON-8	6N04L020

最大额定值，在 $T_j=25^\circ\text{C}$ 时，除非另有规定

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current ¹⁾	I_D	$T_c=25^\circ\text{C}, V_{GS}=10\text{V}$	100	A
		$T_c=100^\circ\text{C}, V_{GS}=10\text{V}^{2)}$	100	
Pulsed drain current ²⁾	$I_{D,pulse}$	$T_c=25^\circ\text{C}$	400	
Avalanche energy, single pulse ²⁾	E_{AS}	$I_D=20\text{A}, R_{G,min}=25\Omega$	147	mJ
Avalanche current, single pulse	I_{AS}	$R_{G,min}=25\Omega$	20	A
Gate source voltage	V_{GS}	-	±16	V
Power dissipation	P_{tot}	$T_c=25^\circ\text{C}$	75	W

本数据手册的原文使用英文撰写。为方便起见，英飞凌提供了译文；由于翻译过程中可能使用了自动化工具，英飞凌不保证译文的准确性。为确认准确性，请务必访问 infineon.com 参考最新的英文版本（控制文档）。

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

热特性²⁾

Thermal resistance, junction - case	R_{thJC}	-	-	-	2.0	K/W
Thermal resistance, junction - ambient	R_{thJA}	6 cm ² cooling area ³⁾	-	-	50	

电气特性，在 $T_j = 25^\circ\text{C}$ 时，除非另有说明

静态参数特性

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=1mA$	40	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=32\mu A$	1.2	1.6	2.0	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=40V, V_{GS}=0V, T_j=25^\circ\text{C}$	-	-	1	μA
		$V_{DS}=40V, V_{GS}=0V, T_j=125^\circ\text{C}^{2)}$	-	-	10	
Gate-source leakage current	I_{GSS}	$V_{GS}=16V, V_{DS}=0V$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=50A$	-	2.26	2.70	m Ω
		$V_{GS}=10V, I_D=50A$	-	1.66	2.04	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

动态参数特性²⁾

Input capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=25V,$ $f=1MHz$	-	2111	2744	pF
Output capacitance	C_{oss}		-	587	763	
Reverse transfer capacitance	C_{rss}		-	35	53	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=20V, V_{GS}=10V,$ $I_D=100A, R_G=3.5\Omega$	-	4	-	ns
Rise time	t_r		-	2	-	
Turn-off delay time	$t_{d(off)}$		-	18	-	
Fall time	t_f		-	8	-	

栅极电荷特性²⁾

Gate to source charge	Q_{gs}	$V_{DD}=32V, I_D=100A,$ $V_{GS}=0 \text{ to } 10V$	-	6.6	8.7	nC
Gate to drain charge	Q_{gd}		-	6.7	10.1	
Gate charge total	Q_g		-	34	46	
Gate plateau voltage	$V_{plateau}$		-	3.1	-	V

反向二极管

Diode continuous forward current ²⁾	I_s	$T_C=25^\circ C$	-	-	100	A
Diode pulse current ²⁾	$I_{S,pulse}$		-	-	400	
Diode forward voltage	V_{SD}	$V_{GS}=0V, I_F=50A,$ $T_j=25^\circ C$	-	0.8	1.1	V
Reverse recovery time ²⁾	t_{rr}	$V_R=20V, I_F=50A,$ $di_F/dt=100A/\mu s$	-	28	-	ns
Reverse recovery charge ²⁾	Q_{rr}		-	15	-	nC

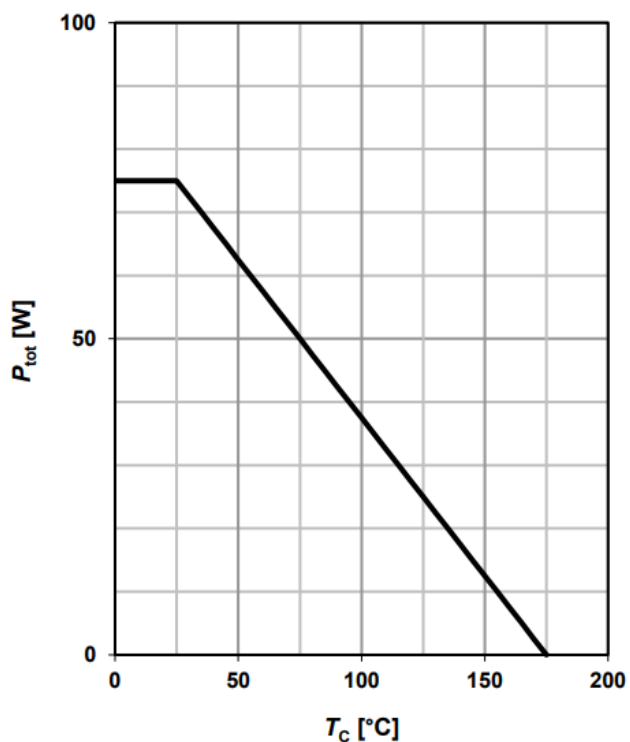
¹⁾ 电流受封装限制；当 $R_{thJC} = 2.0 \text{ K/W}$ 时，该芯片在 $25^\circ C$ 时能够承载 144 A。

²⁾ 这些参数不经过生产测试，但经过设计和/或特性验证。

³⁾ 器件安装在 $40 \text{ mm} \times 40 \text{ mm} \times 1.5 \text{ mm}$ 环氧树脂印刷电路板 FR4 上，漏极连接用铜面积为 6 cm^2 （一层， $70 \mu\text{m}$ 厚）。印刷电路板垂直放置在静止空气中。

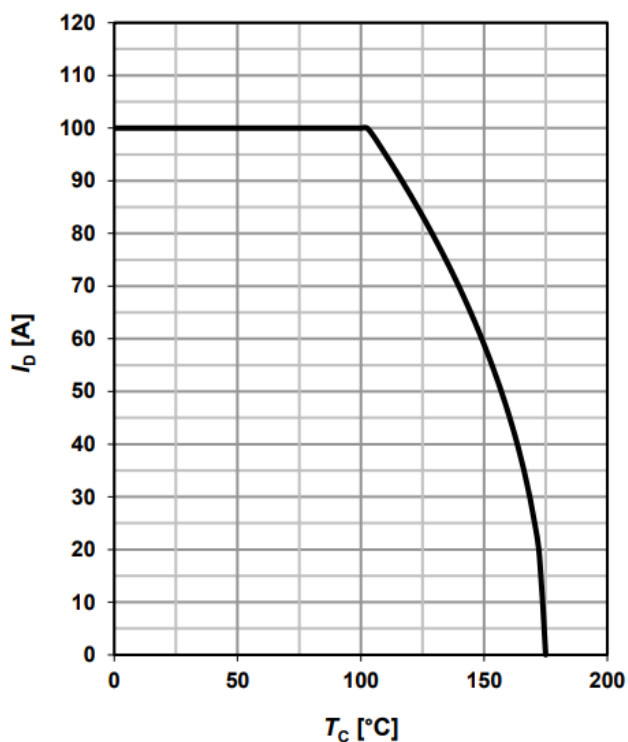
1 功率耗散

$$P_{\text{tot}} = f(T_c); V_{\text{GS}} = 10 \text{ V}$$



2 漏极电流

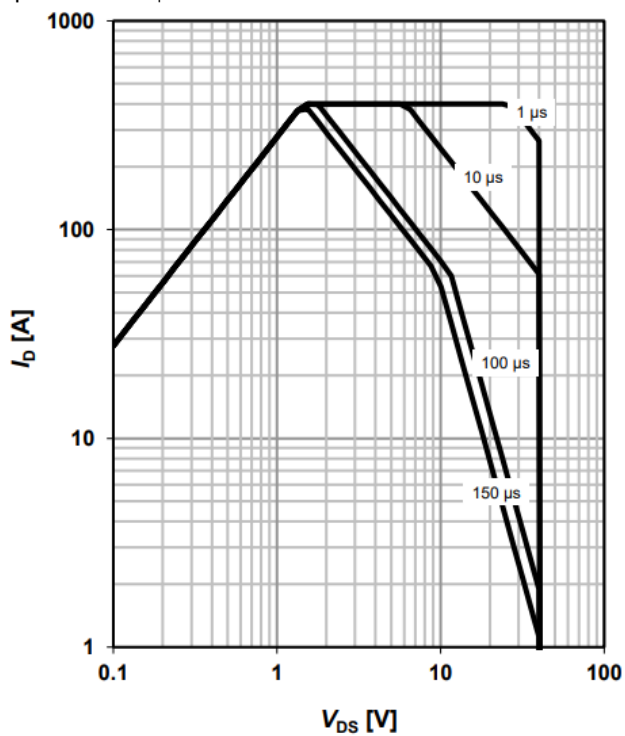
$$I_D = f(T_c); V_{\text{GS}} = 10 \text{ V}$$



3 安全工作区

$$I_D = f(V_{\text{DS}}); T_c = 25 \text{ °C}; D = 0$$

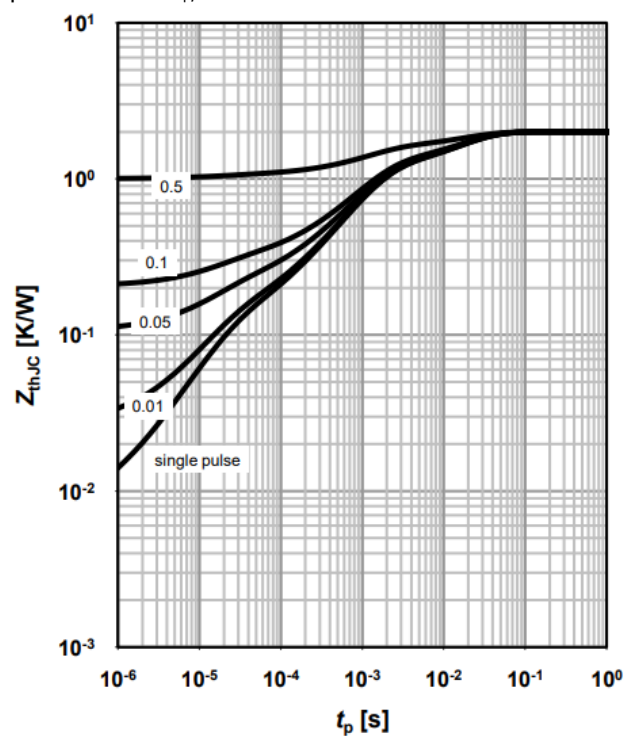
parameter: t_p



4 最大瞬态热阻抗

$$Z_{\text{thJC}} = f(t_p)$$

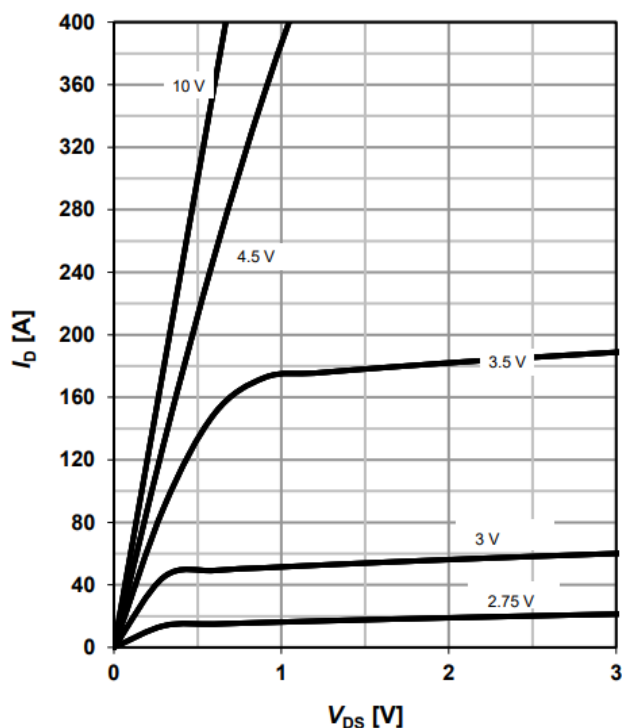
parameter: $D = t_p/T$



5 典型输出特性

$$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$$

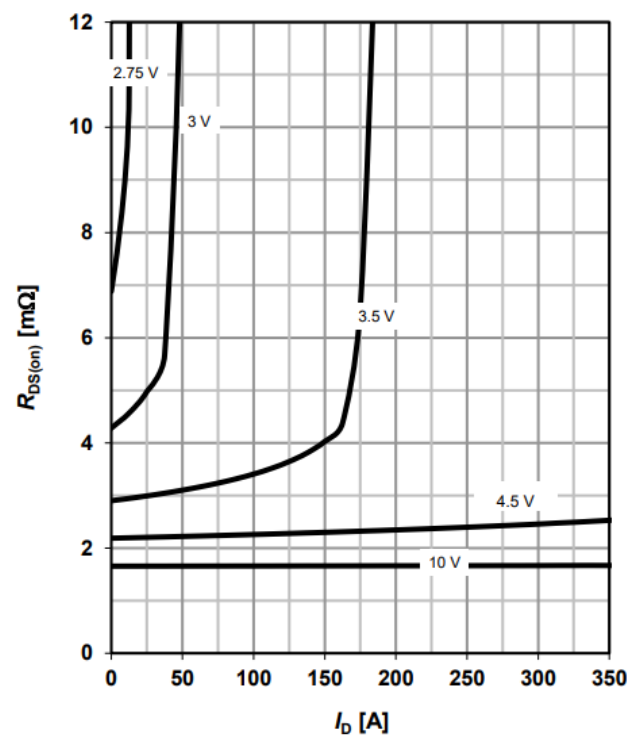
parameter: V_{GS}



6 典型漏源导通电阻

$$R_{DS(on)} = f(I_D); T_j = 25^\circ\text{C}$$

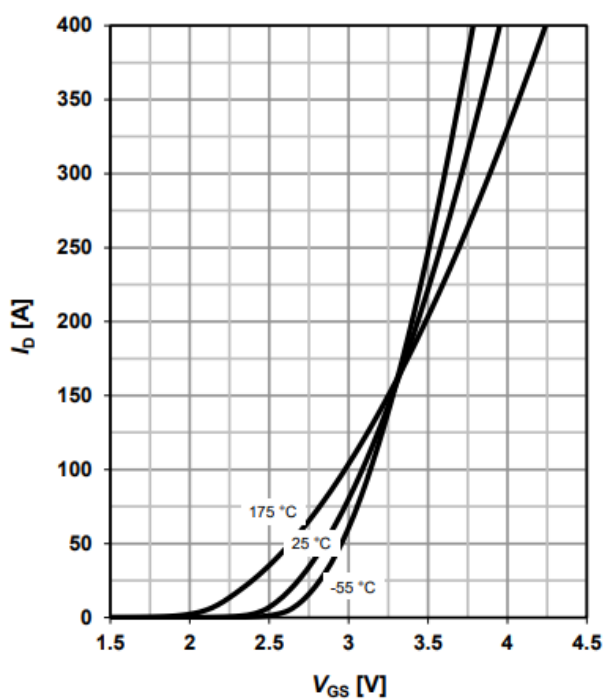
parameter: V_{GS}



7 典型转移特性

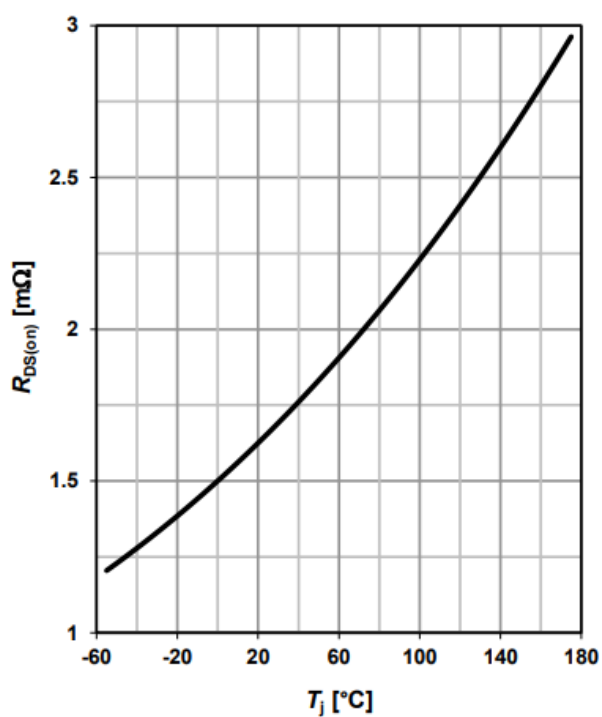
$$I_D = f(V_{GS}); V_{DS} = 6\text{ V}$$

parameter: T_j



8 典型漏源导通电阻

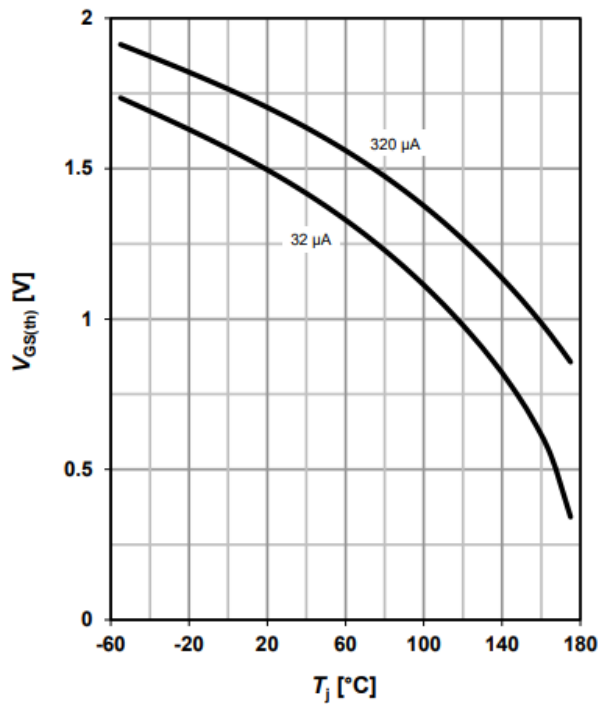
$$R_{DS(on)} = f(T_j); I_D = 50\text{ A}; V_{GS} = 10\text{ V}$$



9 典型栅极阈值电压

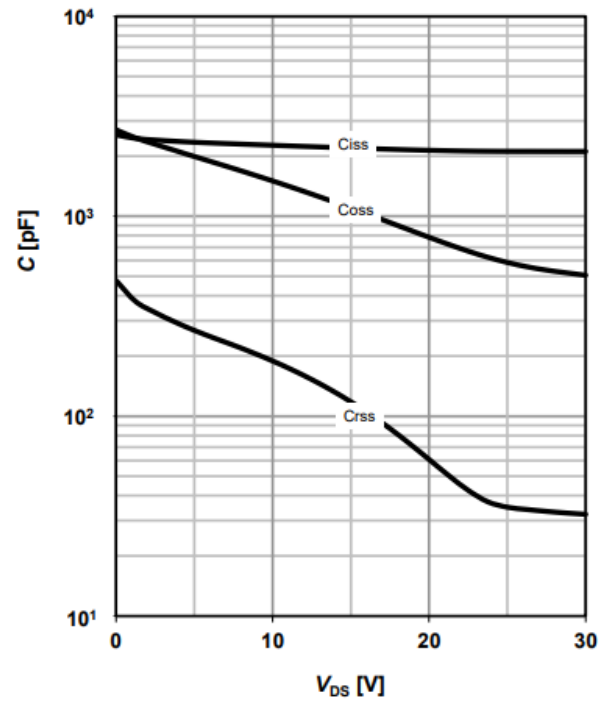
$$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$$

parameter: I_D



10 典型电容值

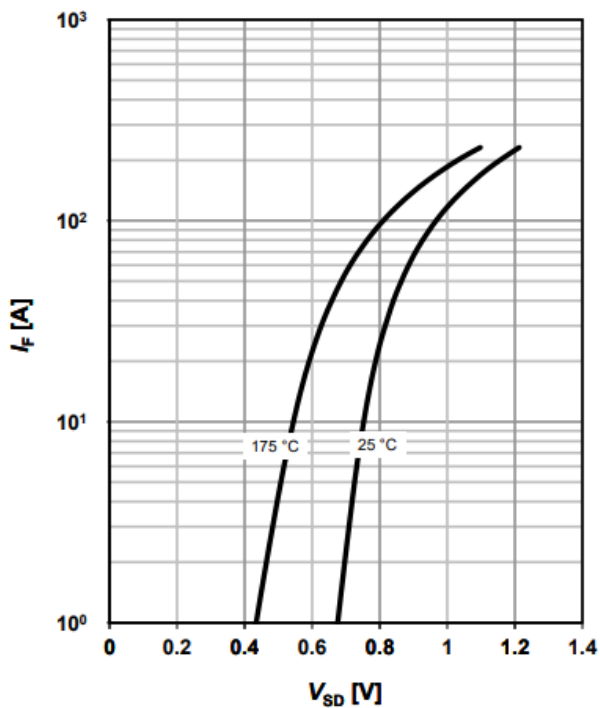
$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$



11 典型二极管正向导通特性

$$I_F = f(V_{SD})$$

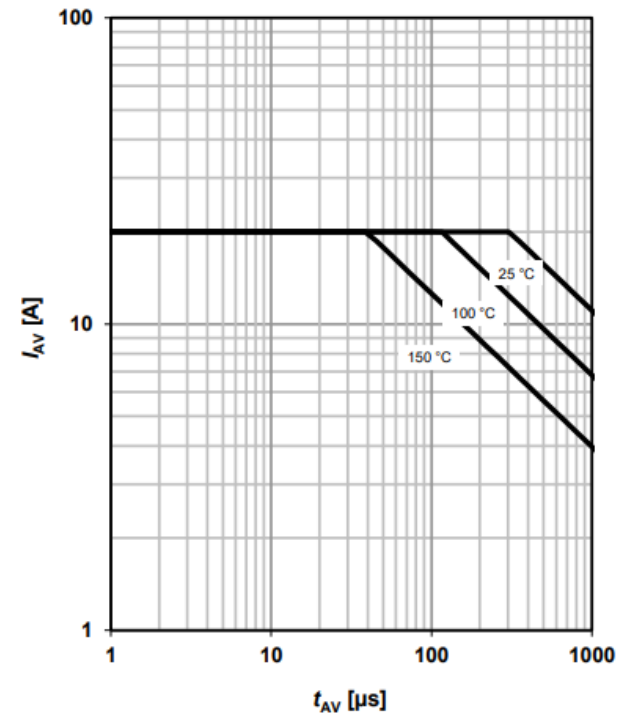
parameter: T_j



12 典型雪崩特性

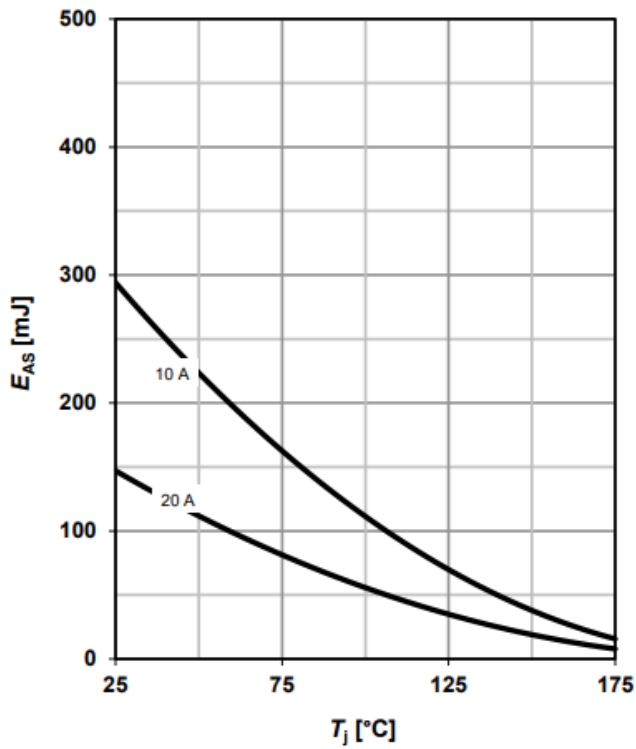
$$I_{AS} = f(t_{AV})$$

parameter: $T_{j(start)}$



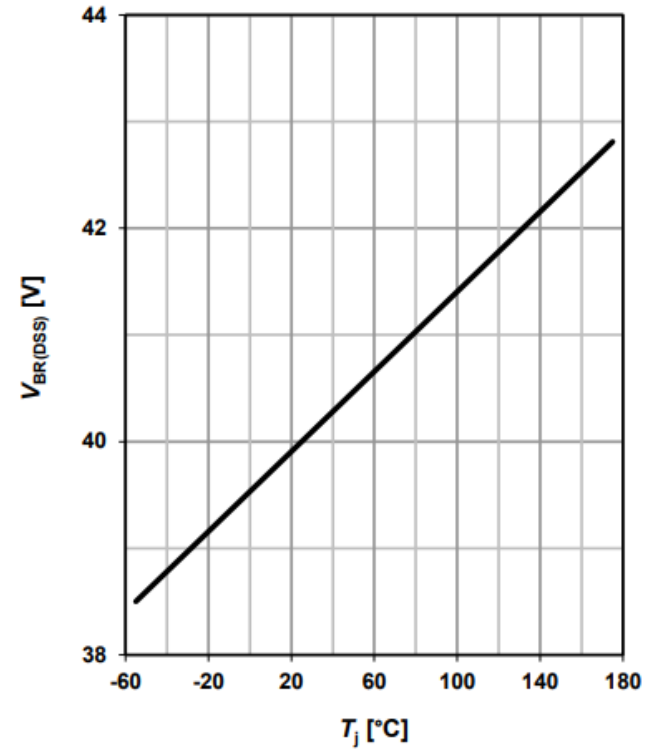
13 典型雪崩能量

$$E_{AS} = f(T_j)$$



14 漏源击穿电压

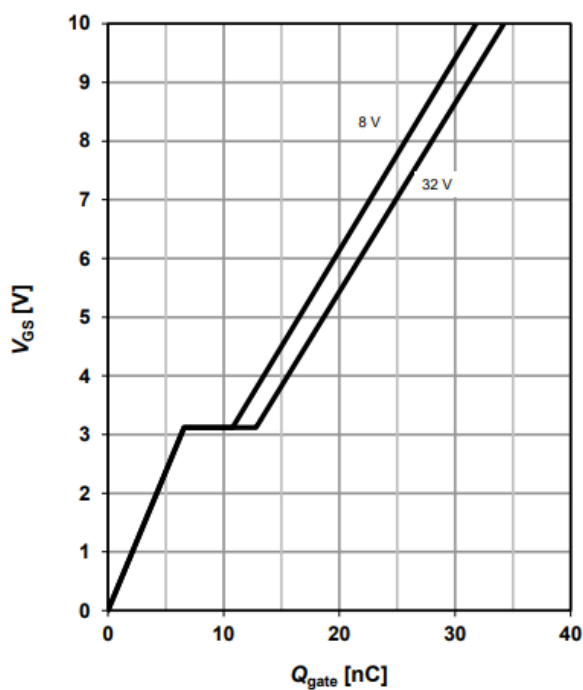
$$V_{BR(DSS)} = f(T_j); I_D = 1 \text{ mA}$$



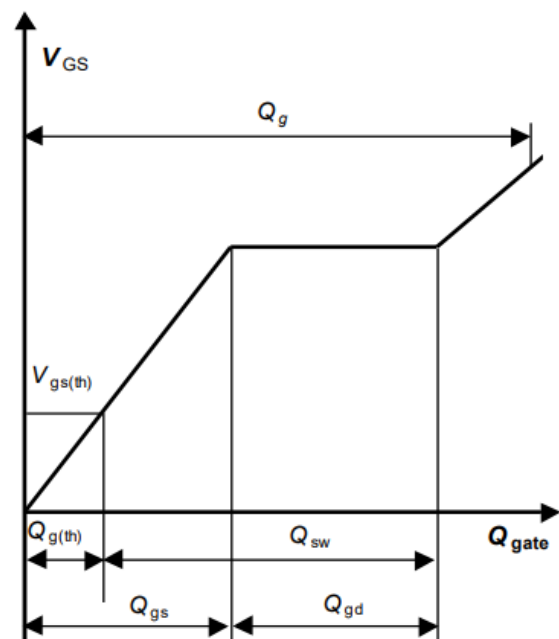
15 典型栅极电荷

$$V_{GS} = f(Q_{gate}); I_D = 100 \text{ A pulsed}$$

parameter: V_{DD}



16 栅极充电波形



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Revision History

Version	Date	Changes



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